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Power Matters[™]

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Overview Diagrams

Collector to Emitter Saturation Voltage

DC Current Gain	HFE	HFE 50.0				150.00	
Maximum Electrical Rating		Symbo	ol	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)		V _{BR(CBO)}				100.00	V
Collector Current (dc)		I _C				5.00	Α
Collector-Emitter Voltage (Base Open)		V _{CEO}				60.00	V
Emitter-Base Voltage (Collector Open)		V _{EBO}				6.00	V
Power Dissipation, Total		P _T				1.50	W

V_{CE(sat)}

This part can be found in the following product categories:

- → Discretes → Transistors → BJT(BiPolar Junction Transistor) → PNP Transistor
- Non-Radiation Hardened Devices ▶ Transistors ▶ BJT(BiPolar Junction Transistor) ▶ NPN Transistor

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